

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or unavteries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor and is officers, employees, uniotificated use, even if such claim any manner.

FAIRCHILD

SEMICONDUCTOR®

November 2013

FQB9P25 — P-Channel QFET[®] MOSFET

FQB9P25

P-Channel QFET[®] MOSFET

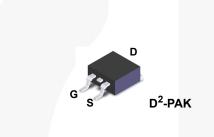
-250 V, -9.4 A, 620 mΩ

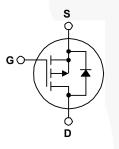
Description

These P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology is especially tailored to minimize on-state resistance, provide superior switching performance, and withstand a high energy pulse in the avalanche and commutation modes. These devices are well suited for high efficiency switching DC/DC converters.

Features

- 9.4 A, -250 V, $R_{DS(on)}$ = 620 m Ω (Max.) @ V_{GS} = -10 V, I_{D} = -4.7 A
- Low Gate Charge (Typ. 29 nC)
- Low Crss (Typ. 27 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

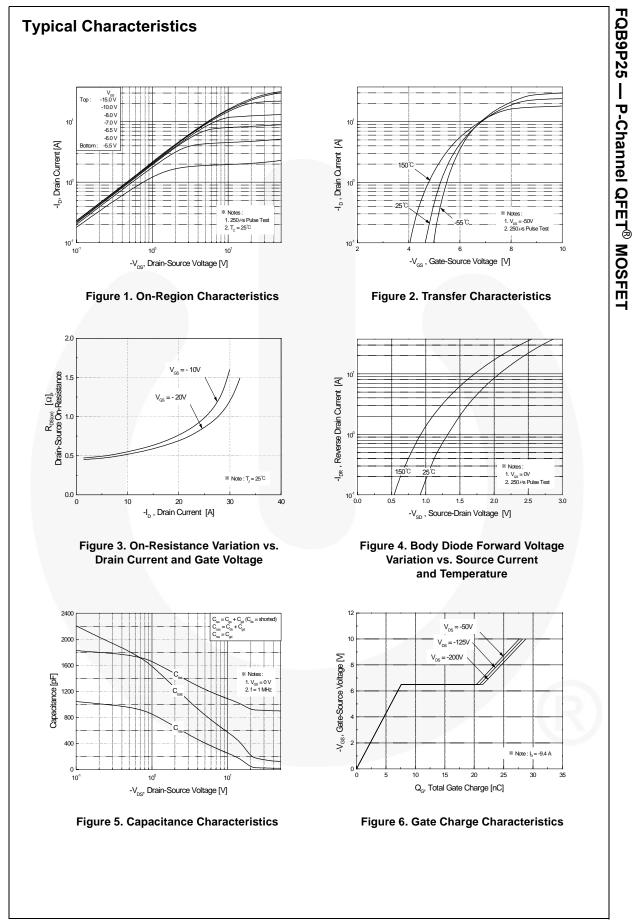
Symbol	Parameter	FQB9P25TM	Unit			
V _{DSS}	Drain-Source Voltage	-250	V			
I _D	Drain Current - Continuous ($T_C = 25^\circ$	-9.4	А			
	- Continuous (T _C = 100	-5.9	A			
I _{DM}	Drain Current - Pulsed	(Note 1) -37.6		A		
V _{GSS}	Gate-Source Voltage		± 30	V		
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	650	mJ		
I _{AR}	Avalanche Current	(Note 1)	-9.4	A		
E _{AR}	Repetitive Avalanche Energy	(Note 1)	12	mJ		
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	(Note 3) -5.5			
P _D	Power Dissipation ($T_A = 25^{\circ}C$) *	3.13	W			
	Power Dissipation ($T_C = 25^{\circ}C$)	120	W			
	- Derate above 25°C	0.96	W/°C			
T _J , T _{STG}	Operating and Storage Temperature Rai	-55 to +150	°C			
Τ _L	Maximum lead temperature for soldering 1/8" from case for 5 seconds	300	°C			

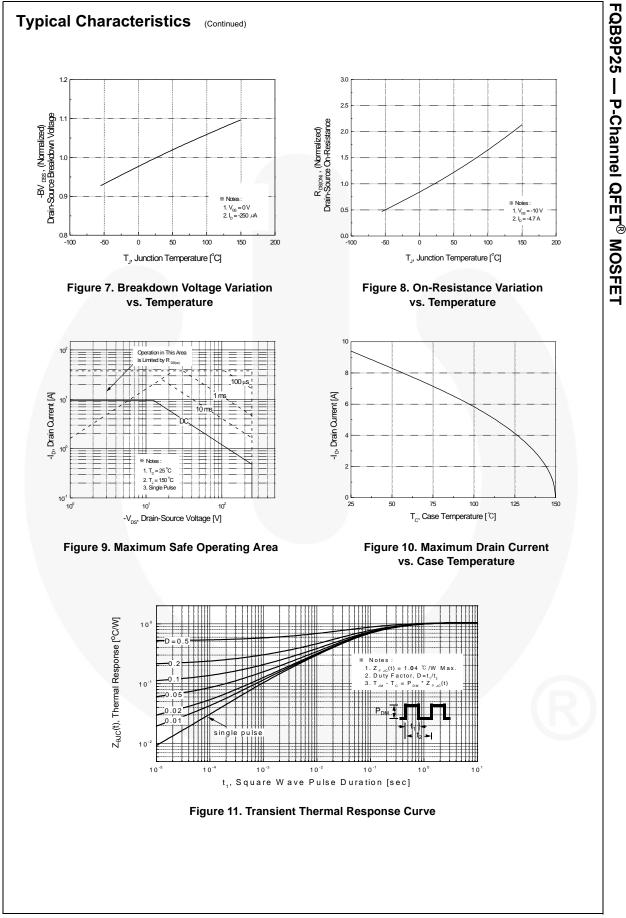
Thermal Characteristics

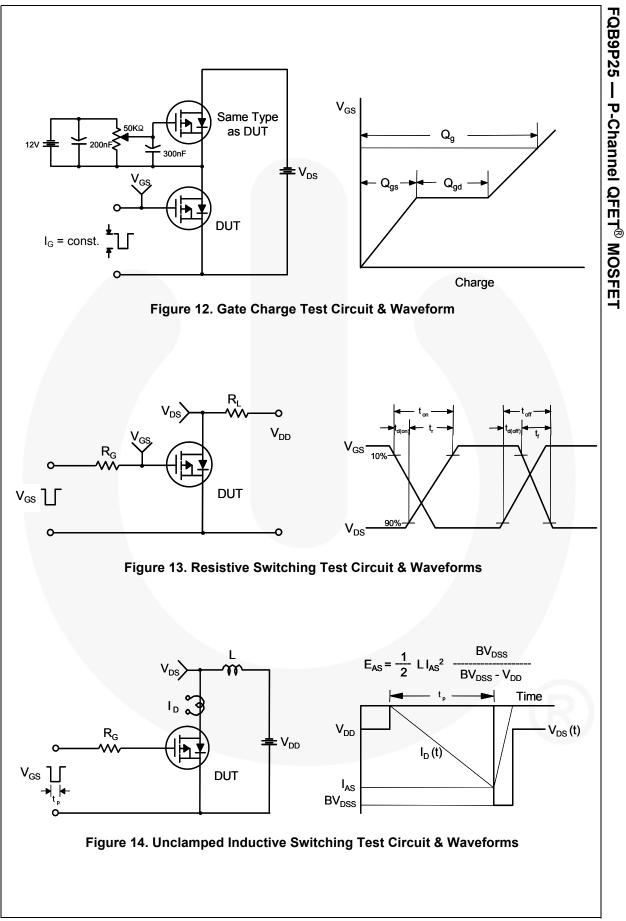
Symbol	Parameter	FQB9P25TM	Unit		
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max. 1.04				
R_{\thetaJA}	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	°C/W		
	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	40			

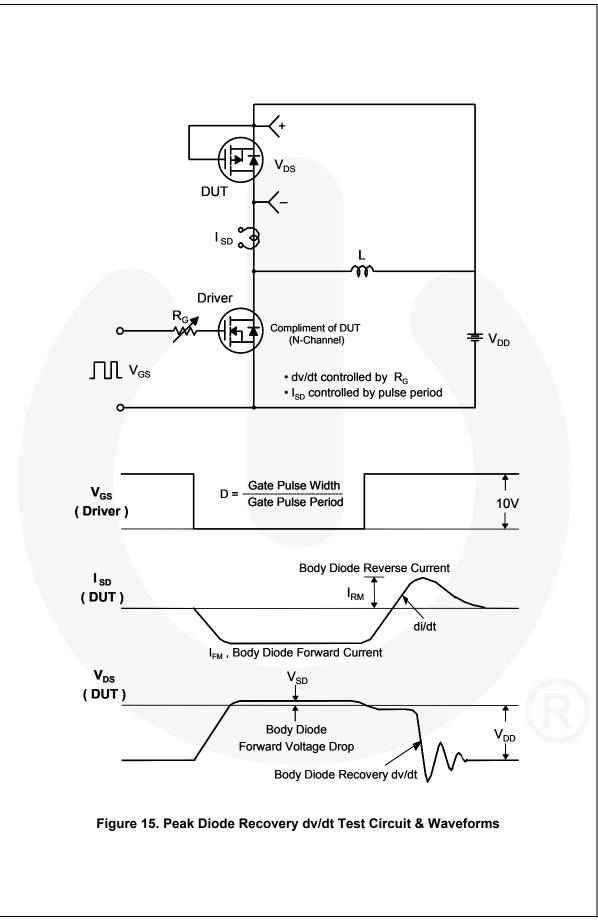
-				kage Packing Method Reel			Tape Width 24 mm		Quantity 800 units		
		D ² -F	PAK Tape and Reel 330			mm					
Electri	cal Ch	aracteristics 1	- _c = 25°C un	less otherv	vise noted.						
Symbol		Parameter			Test Cond	litions		Min	Тур	Мах	Unit
Off Cha	rootori	ation									
BV _{DSS}		ource Breakdown Volta	200	Vee -	$0 \sqrt{1} = -25$	0.114		-250			V
ΔBV_{DSS}			0	$V_{GS} = 0 V, I_D = -250 \mu A$			-250			v	
$/ \Delta T_{J}$	Breakdown Voltage Temperature Coefficient		$I_D = -250 \ \mu\text{A}$, Referenced to 25°C				-0.2		V/°C		
I _{DSS}	Zero Gate Voltage Drain Current		ont		-250 V, V _{GS}					-1	μA
			V _{DS} = -200 V, T _C = 125°C					-10	μA		
I _{GSSF}	Gate-Bo	dy Leakage Current, I	Forward		$V_{GS} = -30 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$					-100	nA
I _{GSSR}	Gate-Bo	dy Leakage Current, I	Reverse	V _{GS} =	30 V, V _{DS} =	0 V		-		100	nA
On Cha	racteris	stics									
V _{GS(th)}		reshold Voltage		V _{DS} =	V _{GS} , I _D = -2	50 µA	-	-3.0		-5.0	V
R _{DS(on)}	Static D On-Resi	rain-Source stance		V _{GS} =	-10 V, I _D = -	4.7 A			0.48	0.62	Ω
9 _{FS}		Transconductance	_	V _{DS} =	-40 V, I _D = -	4.7 A			5.7		S
				1							
-	1	acteristics		1							
Ciss	· ·	pacitance	_	V _{DS} =	-25 V, V _{GS} = 0 V,			910	1180		
C _{oss}		Capacitance		f = 1.0	MHz				170	220	pF
C _{rss}	Reverse	Transfer Capacitance	•						27	35	pF
Switchi	ing Cha	racteristics									
t _{d(on)}	Turn-On	Delay Time		Vaa -	-125 V In -	-944			20	50	ns
t _r	Turn-On	Rise Time		$V_{DD} = -125 \text{ V}, \text{ I}_{D} = -9.4 \text{ A},$			150	310	ns		
t _{d(off)}	Turn-Off	Delay Time		- KG - 2	$R_{G} = 25 \Omega$			45	100	ns	
t _f	Turn-Off	Fall Time				1)	Note 4)		65	140	ns
Qg	Total Ga	te Charge		V _{DS} =	-200 V, I _D =	-9.4 A.			29	38	nC
Q _{gs}	Gate-Sc	urce Charge		$V_{GS} = -10 V$			7.6		nC		
Q _{gd}	Gate-Dr	ain Charge				1)	Note 4)	-	14		nC
		Diode Characteri	stics c	ad Mar	imum Br	tinco					
I _S		m Continuous Drain-S				ungs	-			-9.4	A
I _{SM}		m Pulsed Drain-Sourc							-37.6		
V _{SD}		ource Diode Forward				4 A				-5.0	V
t _{rr}		Recovery Time	. shage	$V_{GS} = 0 V, I_S = -9.4 A$ $V_{GS} = 0 V, I_S = -9.4 A,$			190	-0.0	ns		
Q _{rr}	_	Recovery Charge		V _{GS} = 0 V, I _S = -9.4 A, dI _F / dt = 100 A/μs				1.45		μC	
Notes:	11070130	incourse onlarge							1.40		μΟ

FQB9P25 — P-Channel QFET[®] MOSFET









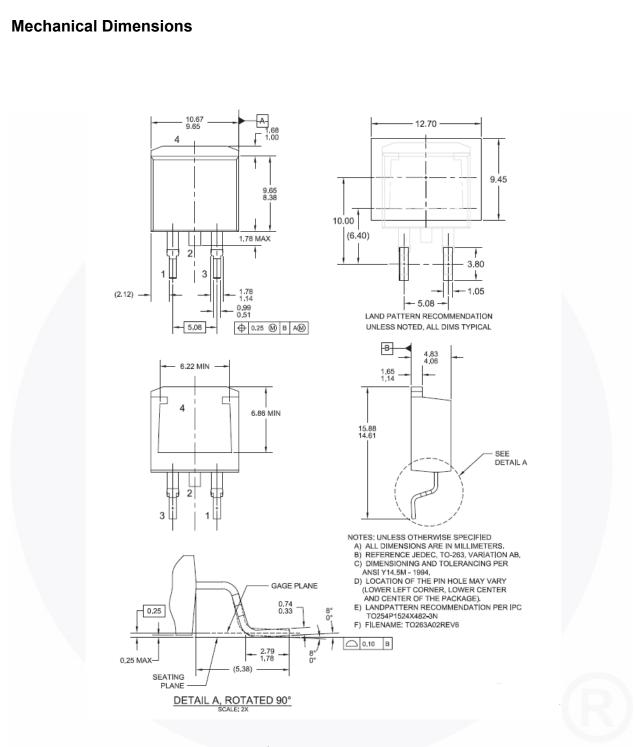


Figure 16. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT263-002

FQB9P25 — P-Channel QFET[®] MOSFET



Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.
	•	Rev

Rev. 166

FQB9P25 —

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor has against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death ass

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below :

614233C 648584F IRFD120 JANTX2N5237 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L SBVS138LT1G 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C BUK954R8-60E NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE222 NTE2384 NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UF0-7B